

TLE4966L

High Precision Hall-Effect Switch with Direction Detection

About this document

Features

- 2.7 V to 24 V supply voltage operation
- Operation from unregulated power supply
- High sensitivity and high stability of the magnetic switching points
- High resistance to mechanical stress by active error compensation
- Reverse battery protection (-18 V)
- Superior temperature stability
- Peak temperatures up to 195°C without damage
- Low jitter (typically 1 μ s)
- Digital output signals
- Bipolar version
- Excellent matching between the 2 Hall probes
- Hall plate distance 1.45 mm
- Direction & speed information
- Direction signal switches before the speed signal



Target applications

The TLE4966L is an integrated circuit double Hall-effect sensor designed specifically for highly accurate applications. Precise magnetic switching points and high temperature stability are achieved by active compensation circuits and chopper techniques on chip. The IC provides a speed signal at Q2 for every magnetic pole pair and a direction information at Q1, which is provided before the speed signal.

| Product type | Package |
|--------------|------------|
| TLE4966L | PG-SSO-4-1 |

Table of contents

| | | |
|----------|--|----|
| | About this document | 1 |
| | Table of contents | 2 |
| 1 | Functional description | 3 |
| 1.1 | Pin configuration (top view) | 3 |
| 2 | General | 4 |
| 2.1 | Block diagram | 4 |
| 2.2 | Circuit description | 4 |
| 3 | Maximum ratings | 5 |
| 3.1 | Absolute maximum ratings | 5 |
| 4 | Operating range | 6 |
| 5 | Electrical and magnetic parameters | 7 |
| 6 | Timing diagrams for the speed and direction | 9 |
| 7 | Package information | 11 |
| 7.1 | Package marking | 11 |
| 7.2 | Distance between chip and package surface | 11 |
| 7.3 | Package outlines | 12 |
| 8 | Revision history | 13 |
| | Disclaimer | 14 |

1 Functional description

1 Functional description

1.1 Pin configuration (top view)

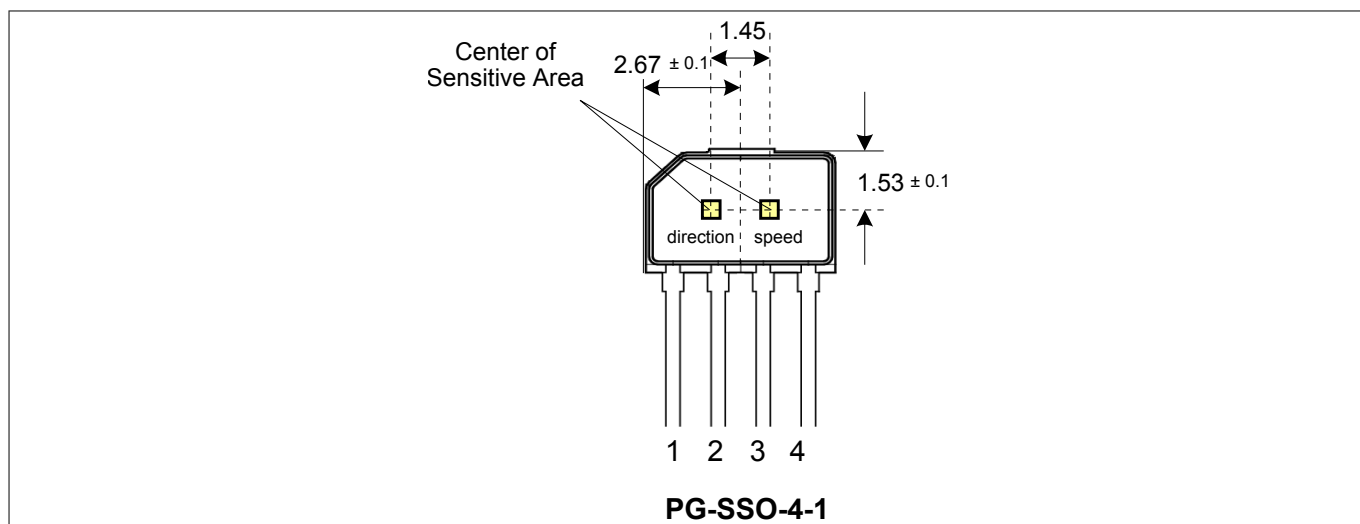


Figure 1 Pin definition and center of sensitive area

Table 1 Pin definitions and functions

| Pin No. | Symbol | Function |
|---------|--------|----------------|
| 1 | V_S | Supply voltage |
| 2 | $Q1$ | Direction |
| 3 | $Q2$ | Speed |
| 4 | GND | Ground |

2 General

2 General

2.1 Block diagram

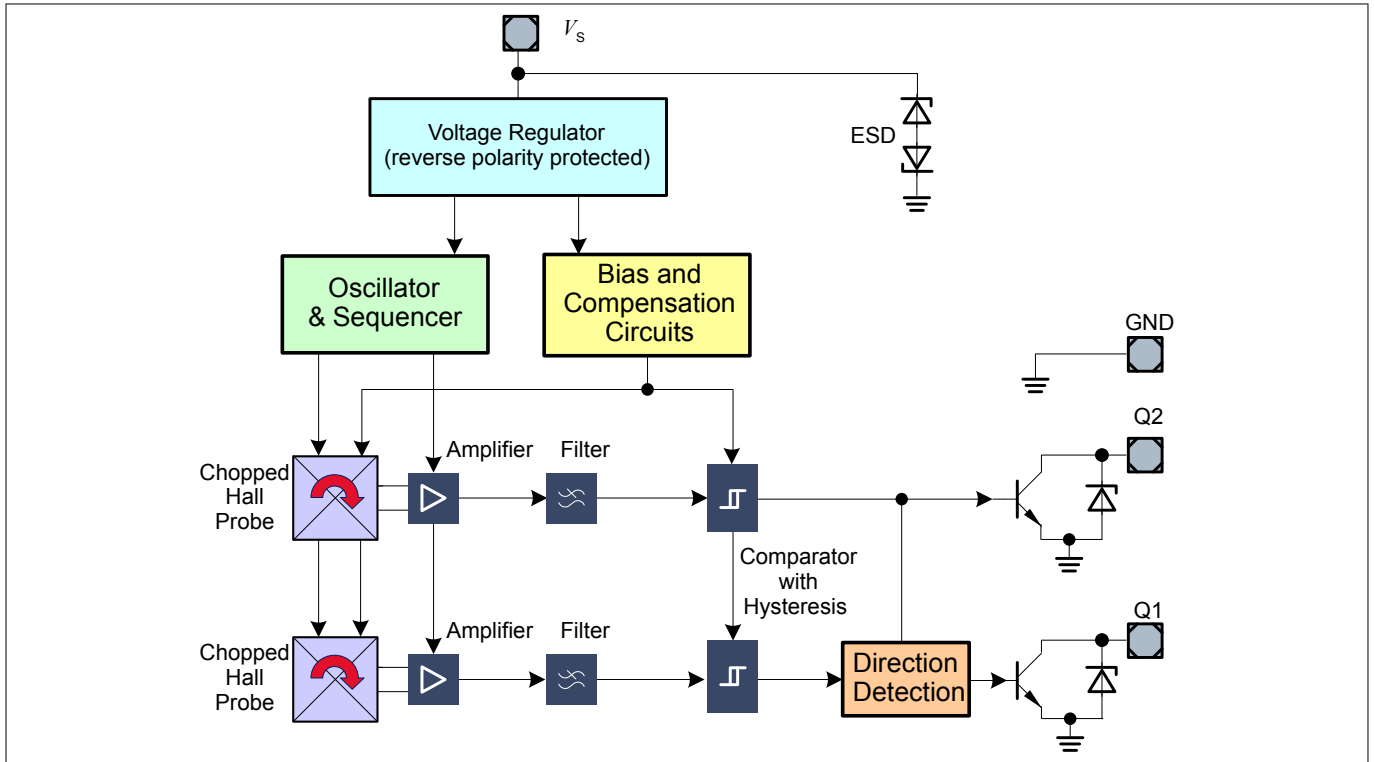


Figure 2 Block diagram

2.2 Circuit description

The chopped Double Hall Switch comprises two Hall probes, bias generator, compensation circuits, oscillator, and output transistors.

The bias generator provides currents for the Hall probes and the active circuits. Compensation circuits stabilize the temperature behavior and reduce technology variations.

The Active Error Compensation rejects offsets in signal stages and the influence of mechanical stress to the Hall probes caused by molding and soldering processes and other thermal stresses in the package. This chopper technique together with the threshold generator and the comparator ensures high accurate magnetic switching points.

3 Maximum ratings

3 Maximum ratings

3.1 Absolute maximum ratings

Table 2 Absolute maximum ratings

$T_j = -40^{\circ}\text{C}$ to 150°C

| Parameter | Symbol | Limit Values | | Unit | Conditions |
|--|--------|--------------|-----------|--------------------|--|
| | | Min. | Max. | | |
| Supply voltage | V_S | -18 | 18 | V | for 1 h, $R_S \geq 200 \Omega$ for 5 min, $R_S \geq 200 \Omega$ |
| | | -18 | 24 | | |
| | | -18 | 26 | | |
| Supply current through protection device | I_S | -50 | 50 | mA | |
| Output voltage | V_Q | -0.7 | 18 | V | for 5 min @ 1.2 k Ω pull up |
| | | -0.7 | 26 | | |
| Continuous output current | I_Q | -50 | 50 | mA | |
| Junction temperature | T_j | - | 155 | $^{\circ}\text{C}$ | for 2000 h (not additive) |
| | | - | 165 | | for 1000 h (not additive) |
| | | - | 175 | | for 168 h (not additive) |
| | | - | 195 | | for 3 x 1 h (additive) |
| Storage temperature | T_S | -40 | 150 | $^{\circ}\text{C}$ | |
| Magnetic flux density | B | - | unlimited | mT | |

Note: Stresses above those listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Table 3 ESD Protection⁽¹⁾

| Parameter | Symbol | Limit Values | | Unit | Notes |
|-------------|------------------|--------------|---------|------|--|
| | | Min. | Max. | | |
| ESD voltage | V_{ESD} | - | ± 4 | kV | HBM, $R = 1.5 \text{ k}\Omega$, $C = 100 \text{ pF}$ $T_A = 25^{\circ}\text{C}$ |

⁽¹⁾ Human Body Model (HBM) tests according to: EOS/ESD Association Standard S5.1-1993 and Mil. Std. 883D method 3015.7

4 Operating range

4 Operating range

Table 4 Operating range

| Parameter | Symbol | Limit Values | | | Unit | Conditions |
|----------------------|--------|--------------|------|------|------|---------------------------------|
| | | Min. | Typ. | Max. | | |
| Supply voltage | V_S | 2.7 | – | 18 | V | |
| | | – | – | 24 | | 1 h with $R_S \geq 200 \Omega$ |
| | | – | – | 26 | | for 5 min $R_S \geq 200 \Omega$ |
| Output voltage | V_Q | -0.7 | – | 18 | V | |
| Junction temperature | T_j | -40 | – | 150 | °C | |
| | | – | – | 175 | | for 168 h |
| Output current | I_Q | 0 | – | 10 | mA | |

5 Electrical and magnetic parameters

5 Electrical and magnetic parameters

Table 5 Electrical characteristics⁽¹⁾

| Parameter | Symbol | Limit Values | | | Unit | Conditions |
|---|-------------|--------------|------|-------------------|---------------------|---|
| | | Min. | Typ. | Max. | | |
| Supply current | I_S | 4 | 5.2 | 7 | mA | $V_S = 2.7 \text{ V} \dots 18 \text{ V}$ |
| Reverse current | I_{SR} | 0 | 0.2 | 1 | mA | $V_S = -18 \text{ V}$ |
| Output saturation voltage | V_{QSAT} | - | 0.3 | 0.6 | V | $I_Q = 10 \text{ mA}$ |
| Output leakage current | I_{QLEAK} | - | 0.05 | 10 | μA | for $V_Q = 18 \text{ V}$ |
| Output fall time | t_f | - | 0.2 | 1 | μs | $R_L = 1.2 \text{ k}\Omega$; $C_L < 50 \text{ pF}$ see Figure 3 |
| Output rise time | t_r | - | 0.2 | 1 | | |
| Chopper frequency | f_{OSC} | - | 320 | - | kHz | |
| Switching frequency | f_{SW} | 0 | - | 15 ⁽²⁾ | kHz | |
| Delay time ⁽³⁾ | t_d | - | 13 | - | μs | |
| Count Signal Delay | t_{dc} | 50 | 200 | 1000 | ns | |
| Output jitter ⁽⁴⁾ | t_{QJ} | - | 1 | - | μs_{RMS} | Typ. value for squarewave signal 1 kHz |
| Repeatability of magnetic thresholds ⁽⁵⁾ | B_{REP} | - | 40 | - | μT_{RMS} | Typ. value for $\Delta B / \Delta t > 12 \text{ mT/ms}$ |
| Power-on time ⁽⁶⁾ | t_{PON} | - | 13 | - | μs | $V_S \geq 2.7 \text{ V}$ |
| Distance of hall plates | d_{HALL} | - | 1.45 | | mm | |
| Thermal resistance ⁽⁷⁾ | R_{thJA} | - | - | -190 | K/W | PG-SSO-4-1 |

- (1) over operating range, unless otherwise specified. Typical values correspond to $V_S = 12 \text{ V}$ and $T_A = 25^\circ\text{C}$
- (2) To operate the sensor at the max. switching frequency, the magnetic signal amplitude must be 1.4 times higher than for static fields. This is due to the -3 dB corner frequency of the low pass filter in the signal path.
- (3) Systematic delay between magnetic threshold reached and output switching
- (4) Jitter is the unpredictable deviation of the output switching delay
- (5) BREP is equivalent to the noise constant
- (6) Time from applying $V_S \geq 2.7 \text{ V}$ to the sensor until the output state is valid
- (7) Thermal resistance from junction to ambient

Calculation of the ambient temperature:

e.g. for $V_S = 12.0 \text{ V}$, $I_{Styp} = 5.5 \text{ mA}$, $V_{QSATtyp} = 0.3 \text{ V}$ and $2 \times I_Q = 10 \text{ mA}$:

Power Dissipation: $P_{DIS} = 72.0 \text{ mW}$.

In $T_A = T_j - (R_{thJA} \times P_{DIS}) = 175^\circ\text{C} - (190 \text{ K/W} \times 0.072 \text{ W})$

Resulting max. ambient temperature: $T_A = 161.3^\circ\text{C}$

5 Electrical and magnetic parameters

Table 6 **Magnetic characteristics⁽¹⁾**

| Parameter | Symbol | T _j [°C] | Limit Values | | | Unit | Conditions |
|---|--------------------|---------------------|--------------|------|------|--------|--|
| | | | Min. | Typ. | Max. | | |
| Operate point | B _{OP} | -40 | 5.2 | 7.7 | 10.3 | mT | |
| | | 25 | 5.0 | 7.5 | 10.0 | | |
| | | 150 | 4.7 | 7.1 | 9.5 | | |
| Release point | B _{RP} | -40 | -10.3 | -7.7 | -5.2 | mT | |
| | | 25 | -10.0 | -7.5 | -5.0 | | |
| | | 150 | -9.5 | -7.1 | -4.7 | | |
| Hysteresis | B _{HYS} | -40 | - | - | - | mT | |
| | | 25 | 10.0 | 15.0 | 20.0 | | |
| | | 150 | - | - | - | | |
| Magnetic matching | B _{MATCH} | -40 | - | - | - | mT | Valid for B _{OP1} - B _{OP2} and B _{RP1} - B _{RP2} |
| | | 25 | -2.0 | 0 | 2.0 | | |
| | | 150 | - | - | - | | |
| Magnetic offset | B _{OFF} | -40 | - | - | - | mT | (B _{OP} + B _{RP}) / 2 |
| | | 25 | -2.0 | 0 | 2.0 | | |
| | | 150 | - | - | - | | |
| Temperature compensation of magnetic thresholds | TC | - | - | -350 | - | ppm/°C | |

(1) over operating range, unless otherwise specified. Typical values correspond to V_S = 12 V

Note: *Typical characteristics specify mean values expected over the production spread*

Field Direction Definition

Positive magnetic fields related with south pole of magnet to the branded side of package.

6 Timing diagrams for the speed and direction

6 Timing diagrams for the speed and direction

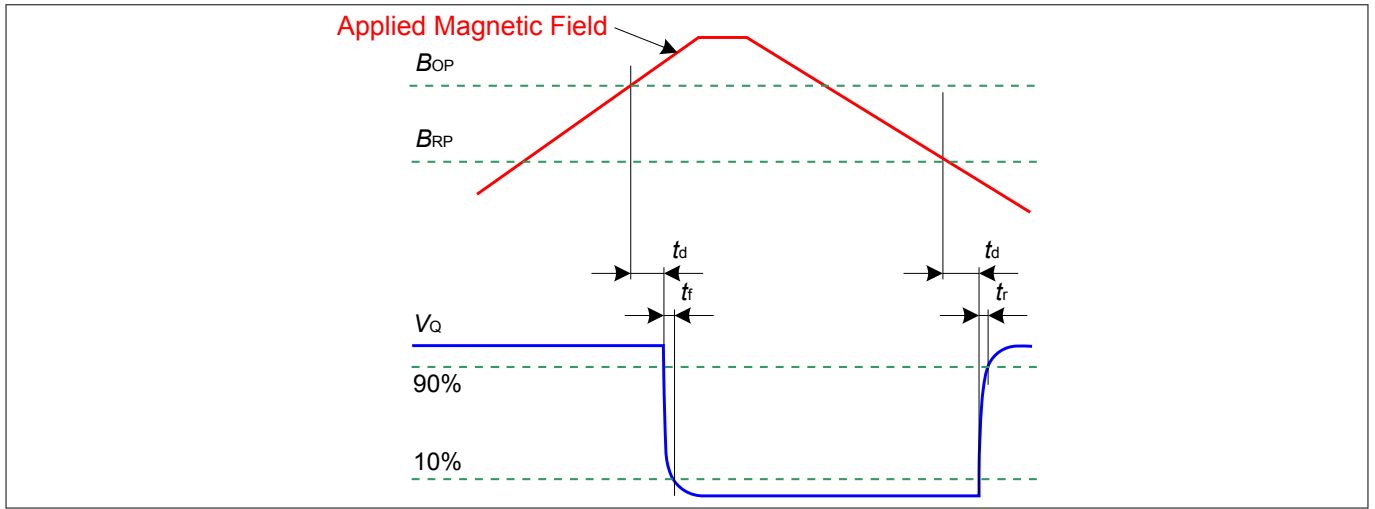


Figure 3 Timing definition of the speed signal

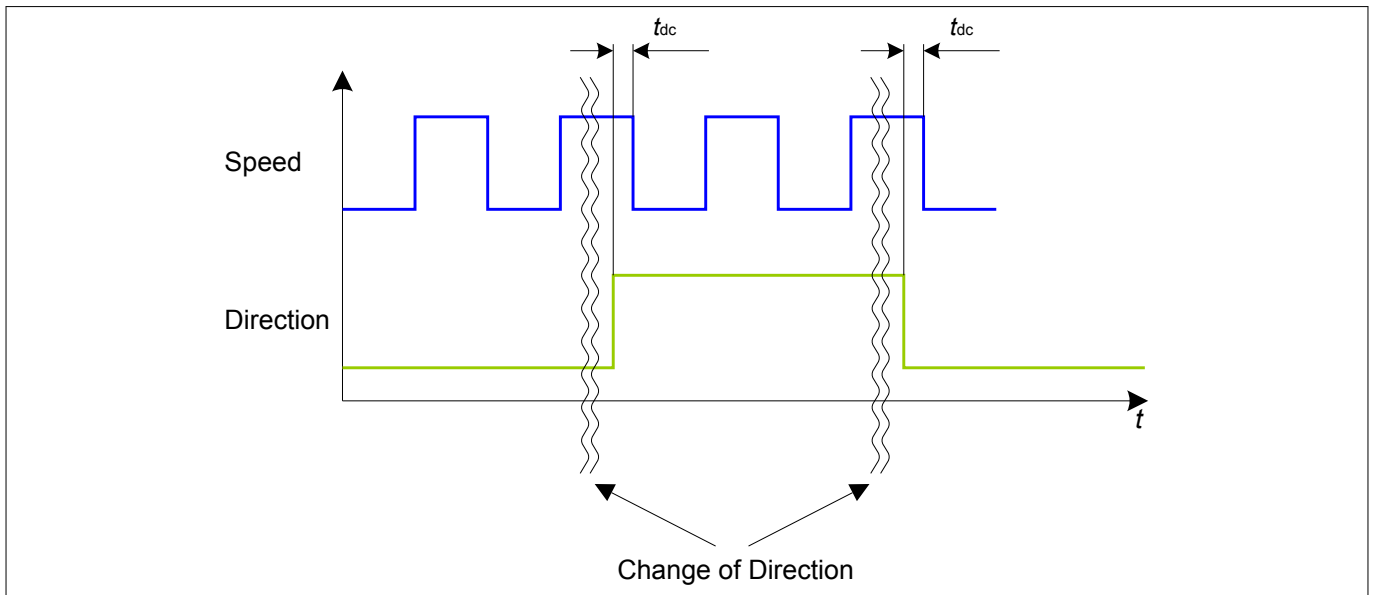


Figure 4 Timing definition of the direction signal

6 Timing diagrams for the speed and direction

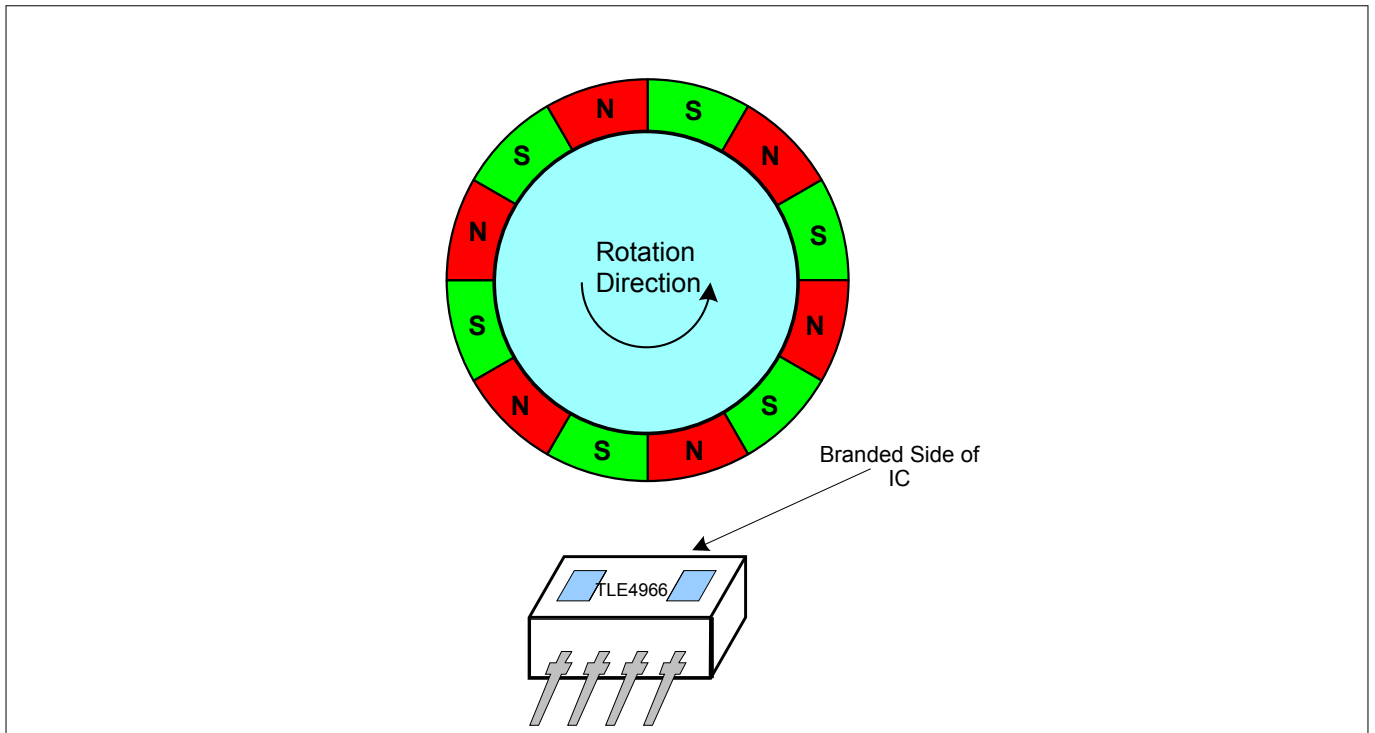


Figure 5 Definition of the direction signal

| Rotation Direction | State of Direction Output V_{Q1} |
|--------------------|------------------------------------|
| Left to right | Low |
| Right to left | High |

7 Package information

7 Package information

7.1 Package marking

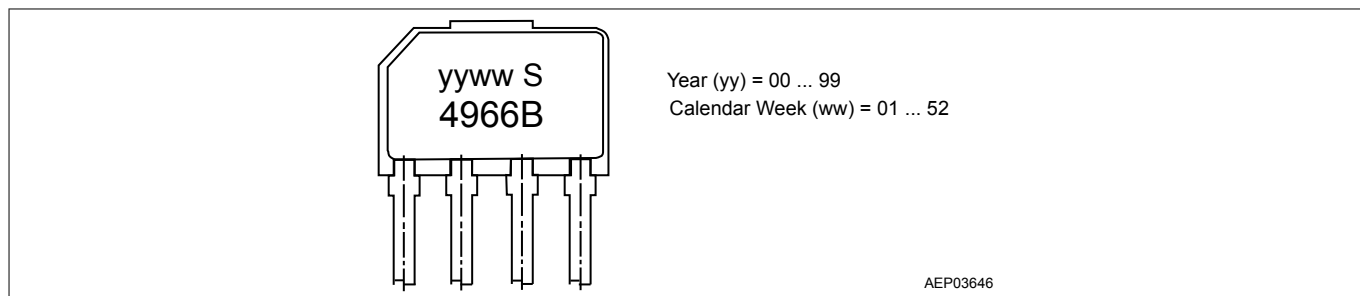


Figure 6 Marking

7.2 Distance between chip and package surface

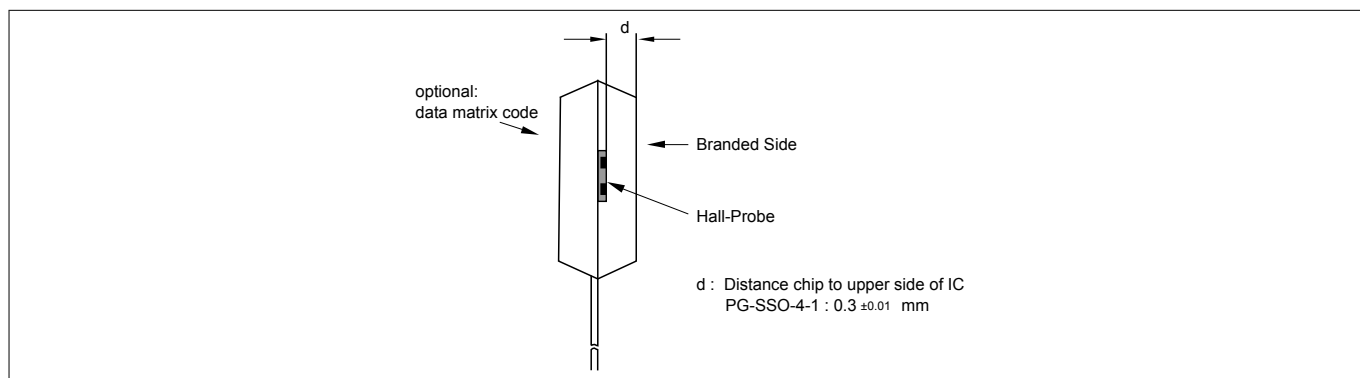


Figure 7 Distance chip to upper side of IC

8 Revision history

8 Revision history

Revision History

| Page | Subjects (major changes since last revision) |
|-------------|---|
|-------------|---|

Revision History: 2020-08, Rev. 2.1

Previous Revisions: Rev. 2.0

| | |
|----|--|
| 11 | Edited figure 7 (optional: data matrix code) |
|----|--|

Trademarks

All referenced product or service names and trademarks are the property of their respective owners.

Edition 2020-08

Published by

Infineon Technologies AG

81726 Munich, Germany

© 2020 Infineon Technologies AG

All Rights Reserved.

Do you have a question about any aspect of this document?

Email: erratum@infineon.com

Document reference

IFX-ipx1597828045356

IMPORTANT NOTICE

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics ("Beschaffheitsgarantie").

With respect to any examples, hints or any typical values stated herein and/or any information regarding the application of the product, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.

In addition, any information given in this document is subject to customer's compliance with its obligations stated in this document and any applicable legal requirements, norms and standards concerning customer's products and any use of the product of Infineon Technologies in customer's applications.

The data contained in this document is exclusively intended for technically trained staff. It is the responsibility of customer's technical departments to evaluate the suitability of the product for the intended application and the completeness of the product information given in this document with respect to such application.

WARNINGS

Due to technical requirements products may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies office.

Except as otherwise explicitly approved by Infineon Technologies in a written document signed by authorized representatives of Infineon Technologies, Infineon Technologies' products may not be used in any applications where a failure of the product or any consequences of the use thereof can reasonably be expected to result in personal injury.

单击下面可查看定价，库存，交付和生命周期等信息

[>>Infineon\(英飞凌\)](#)